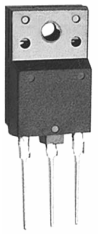
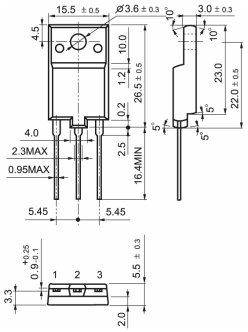
2SD2253 Silicon NPN Triple Diffused Power Transistor

GENERAL DESCRIPTION

HORIZONAL DEFLECTION OUTPUT FOR HIGH RESOLUTION DISPLAY, COLOR TV
High Speed Switching Applications





TO-3PM

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP	MAX	UNIT
V_{CBO}	Collector-Base voltage		-	1700	V
V_{CEO}	Collector-emitter voltage (open base)		-	600	V
I_C	Collector current (DC)		-	6	A
I_{CM}	Collector current peak value		-	12	A
P_{tot}	Total power dissipation	$T_{mb} \leqslant 25℃$	-	50	W
V_{CEsat}	Collector-emitter saturation voltage	I_C = 5.0A; I_B = 1.0A	-	5	V
V_F	Diode forward voltage	I_F = 6.0A	1.6	2.0	V
t_f	Fall time	I_{Csat} = 6.0A; f = 16KHz	0.3	0.7	μs

LIMITING VALUES

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V_{CBO}	Collector-Base voltage		-	1700	V
V_{CEO}	Collector-emitter voltage (open base)		-	600	V
I_C	Collector current (DC)		-	6	A
I_{CM}	Collector current peak value		-	12	A
I_B	Base current (DC)		-	3	A
I_{BM}	Base current peak value		-		A
P_{tot}	Total power dissipation	Tmb≤25℃	-	50	W
T_{stg}	Storage temperature		-55	150	℃
T_j	Junction temperature		-	150	℃

ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	TYP	MAX	UNIT
I_{CE0}	Collector cut-off current	V_{CB} =170 0V; IE=0	-	1.0	mA
V_{CEsat}	Collector-emitter saturation voltages	I_C = 5.0A; I_B = 1.0A	-	5	V
V_{BEsat}	Base-emitter satuation voltage	I_C = 5.0A; I_B = 1.0A	-	1.2	V
h_{FE}	DC current gain	I_C = 1A; V_{CE} = 5V	8	28	
V_F	Diode forward voltage	I_F = 6.0A	1.6	2.0	V
f_T	Transition frequency	I_C = 0.1A; V_{CE} = 10V	1	-	MHz
t					
t_f	Turn-off storage time Turn-off fall time	I_C=6A,$I_{B(end)}$=1.5A,	0.3	0.7	μs

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